

INFORMATION DISCLOSURE CITATION IN AN APPLICATION			ATTY. DOCKET NO. 60188-606	SERIAL NO.			
			APPLICANT Kazuhiko YAMAMOTO				
(PTO-1449)			FILING DATE June 25, 2003	GROUP			
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ₂ (<i>f/k/a</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document			
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FOREIGN PATENT DOCUMENTS							
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qV		Shul-Hsiang Su et al. "A TWO-STEP DEPOSITION TECHNOLOGY FOR HIGH DIELECTRIC CONSTANT HfO ₂ THIN FILMS" <i>Electrochemical and Solid-State Letters</i> , 4(9), 2001, pp. F18-F19.					
qV		Yamamoto et al. "EFFECT OF HF METAL PREDEPOSITION ON THE PROPERTIES OF SPUTTERED HfO ₂ /HF STACKED GATE DIELECTRICS" <i>Applied Physics Letters</i> 81(11), 9 September 2002, pp. 2053-2055					
qV		Byoung Hun Lee et al. "ULTRATHIN HAFNIUM OXIDE WITH LOW LEAKAGE AND EXCELLENT RELIABILITY FOR ALTERNATIVE GATE DIELECTRIC APPLICATION" <i>IEDM</i> , 1999, pp. 133-136.					
EXAMINER			DATE CONSIDERED 04/15/04				

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